

COMPLEMENTARY SILICON POWER TRANSISTOR**Features**

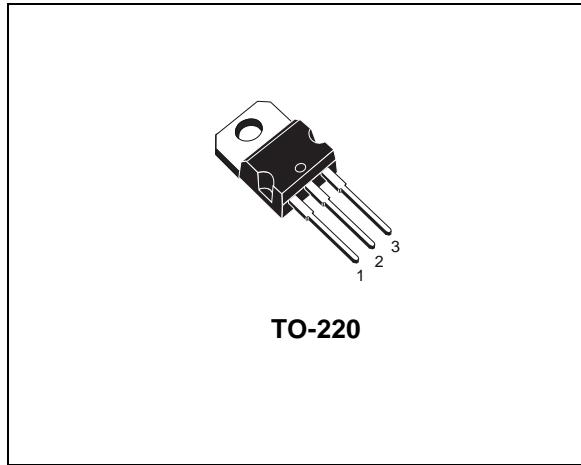
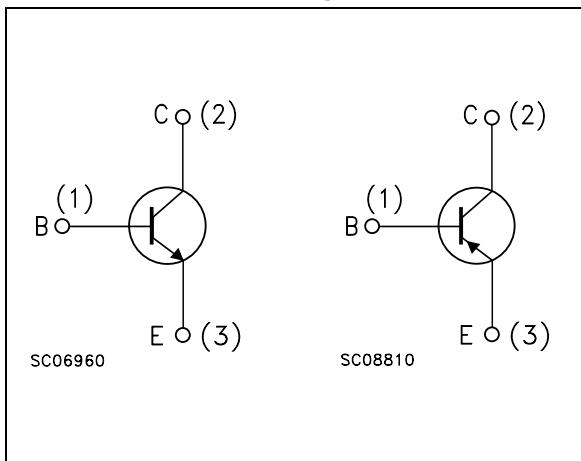
- COMPLEMENTARY PNP-NPN DEVICES
- NEW ENHANCED SERIES
- HIGH SWITCHING SPEED
- h_{FE} IMPROVED LINEARITY

Applications

- GENERAL PURPOSE CIRCUITS
- AUDIO AMPLIFIER
- POWER LINEAR AND SWITCHING

Description

The TIP41A is a silicon base island technology NPN power transistor Jedec TO-220 plastic package with improved performances than the industry standard TIP41A that make this device suitable for audio, power linear and switching applications. The complementary PNP type is TIP42A.

**TO-220****Internal Schematic Diagram****Order Codes**

Part Number	Marking	Package	Packing
TIP41A	TIP41A	TO-220	TUBE
TIP42A	TIP42A	TO-220	TUBE

1 Absolute Maximum Ratings

Table 1. Absolute Maximum Ratings

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage ($I_E = 0$)	60	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	60	V
V_{EBO}	Emitte-Base Voltage ($I_C = 0$)	5	V
I_C	Collector Current	6	A
I_{CM}	Collector Peak Current	10	A
I_B	Base Current	3	mA
P_{TOT}	Total dissipation at $T_{case} = 25^\circ\text{C}$	65	W
	$T_{amb} = 25^\circ\text{C}$	2	W
T_{stg}	Storage Temperature	-65 to 150	$^\circ\text{C}$
T_J	Max. Operating Junction Temperature	150	$^\circ\text{C}$

Note: For PNP types voltage and current values are negative

2 Electrical Characteristics

$T_{case} = 25^\circ\text{C}$; unless otherwise specified

Table 2. Electrical Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CEO}	Collector Cut-off Current ($I_B = 0$)	$V_{CE} = 30\text{ V}$			0.7	mA
I_{EBO}	Emitter Cut-off Current ($I_C = 0$)	$V_{EB} = 5\text{ V}$			1	mA
I_{CES}	Collector Cut-off Current ($V_{BE} = 0$)	$V_{CE} = 60\text{ V}$			0.4	mA
$V_{CEO(sus)}$ <i>Note: 1</i>	Collector-Emitter Sustaining Voltage ($I_B = 0$)	$I_C = 30\text{ mA}$	60			V
$V_{CE(sat)}$ <i>Note: 1</i>	Collector-Emitter saturation Voltage	$I_C = 6\text{ A}$	$I_B = 0.6\text{ A}$		1.5	V
$V_{BE(on)}$ <i>Note: 1</i>	Base-Emitter Voltage	$I_C = 6\text{ A}$	$V_{CE} = 4\text{ V}$		2	V
h_{FE} <i>Note: 1</i>	DC Current Gain	$I_C = 0.3\text{ A}$ $I_C = 3\text{ A}$	$V_{CE} = 4\text{ V}$ $V_{CE} = 4\text{ V}$	30 15	75	
h_{fe}	Small Signal Current Gain	$I_C = 0.5\text{ A}$ $I_C = 0.5\text{ A}$	$V_{CE} = 10\text{ V}$ $V_{CE} = 10\text{ V}$	$f=1\text{ KHz}$ $f=1\text{ KHz}$	20 3	

Note: 1 Pulsed duration = 300 μs , duty cycle $\leq 1.5\%$.

For PNP types voltage e current values are negative.

2.1 Typical Characteristic

Figure 1. DC Current Gain (NPN)

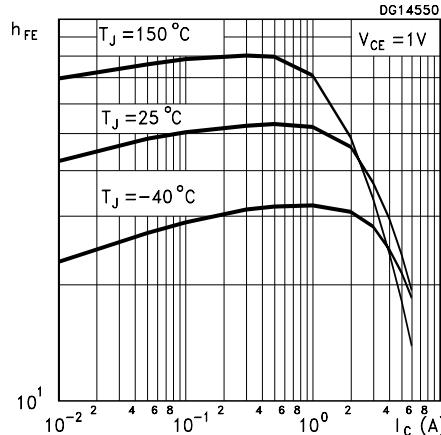


Figure 3. DC Current Gain (NPN)

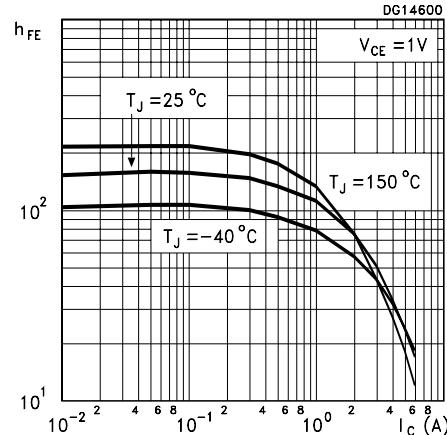


Figure 2. DC Current Gain (PNP)

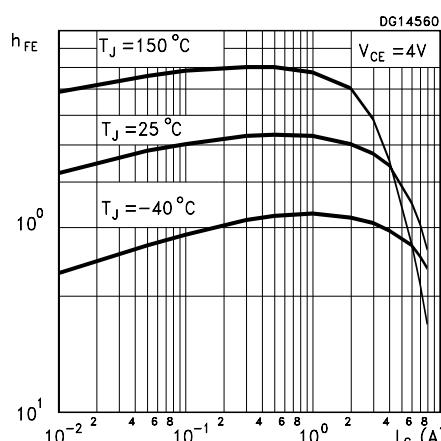


Figure 5. Collector-Emitter Saturation Voltage (NPN) Figure 6. Collector-Emitter Saturation Voltage (PNP)

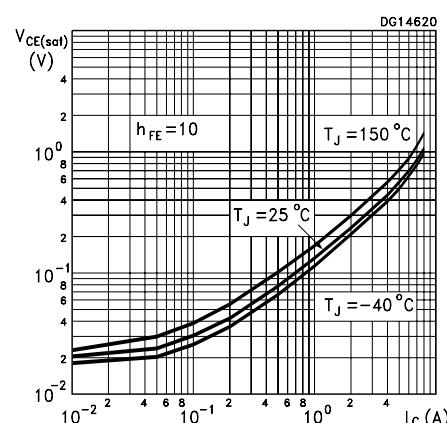
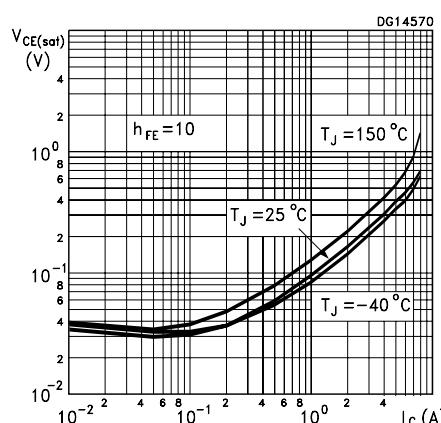
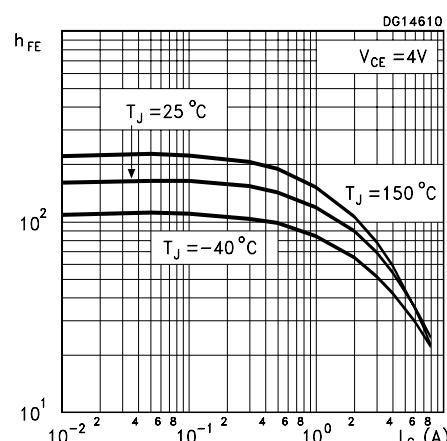


Figure 7. Base-Emitter Saturation Voltage (NPN)

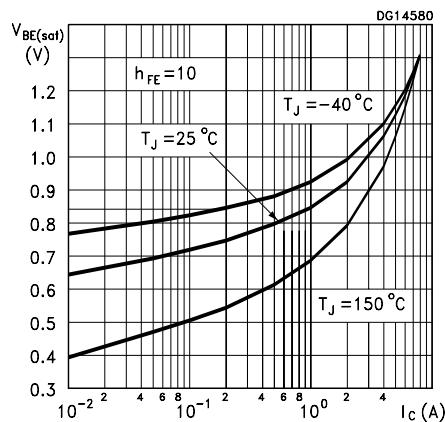


Figure 8. Base-Emitter Saturation Voltage (PNP)

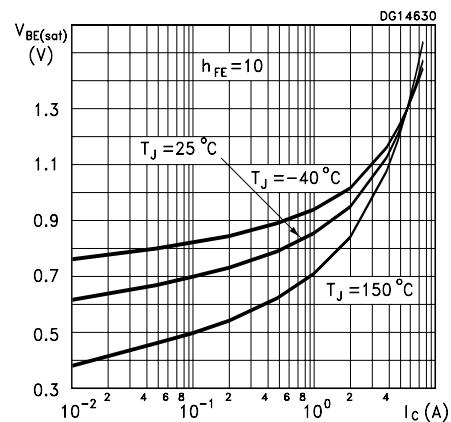


Figure 9. BT_(ON) Time (NPN)

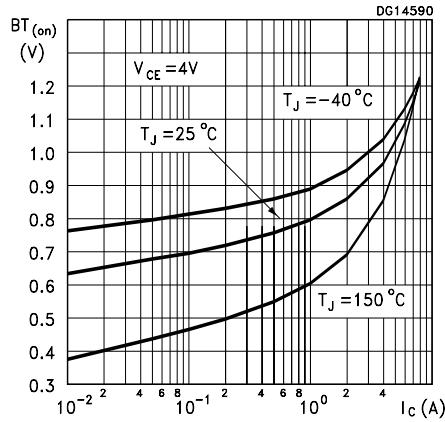


Figure 10. BT_(ON) Time (PNP)

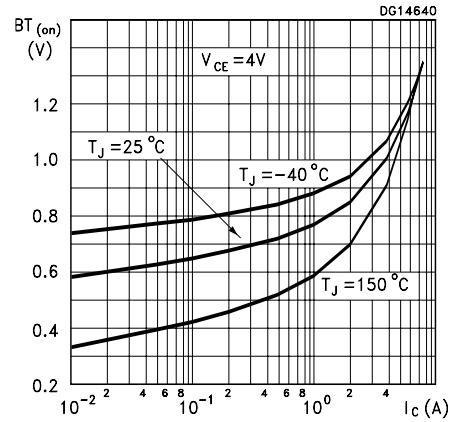


Figure 11. Resistive Load Switching Time (NPN)

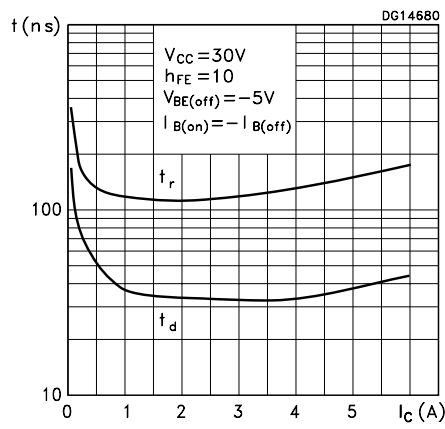


Figure 12. Resistive Load Switching Time (PNP)

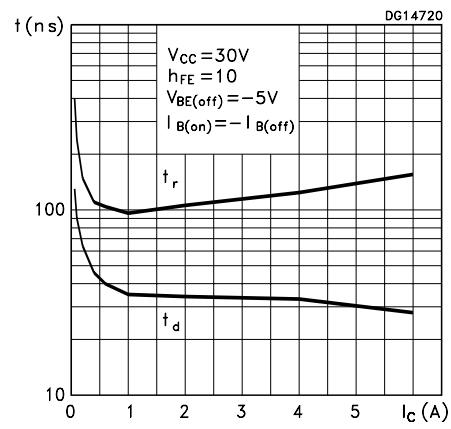


Figure 13. Resistive Load Switching Time (NPN)

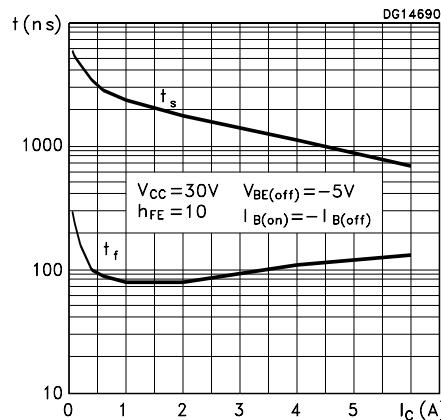


Figure 14. Resistive Load Switching Time (PNP)

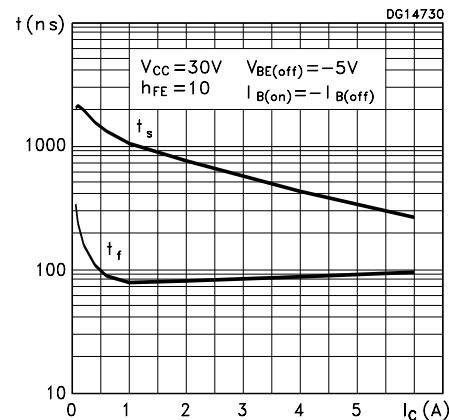


Figure 15. Collector-Base and Collector-Emitter Capacitance (NPN)

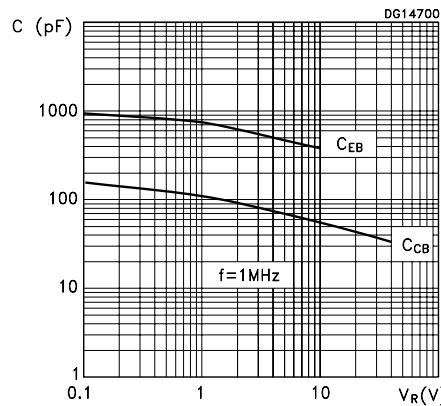
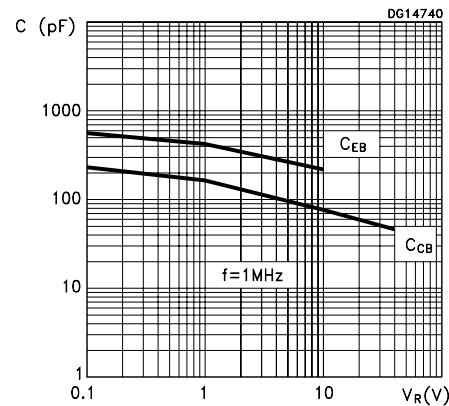


Figure 16. Collector-Base and Collector-Emitter Capacitance (PNP)

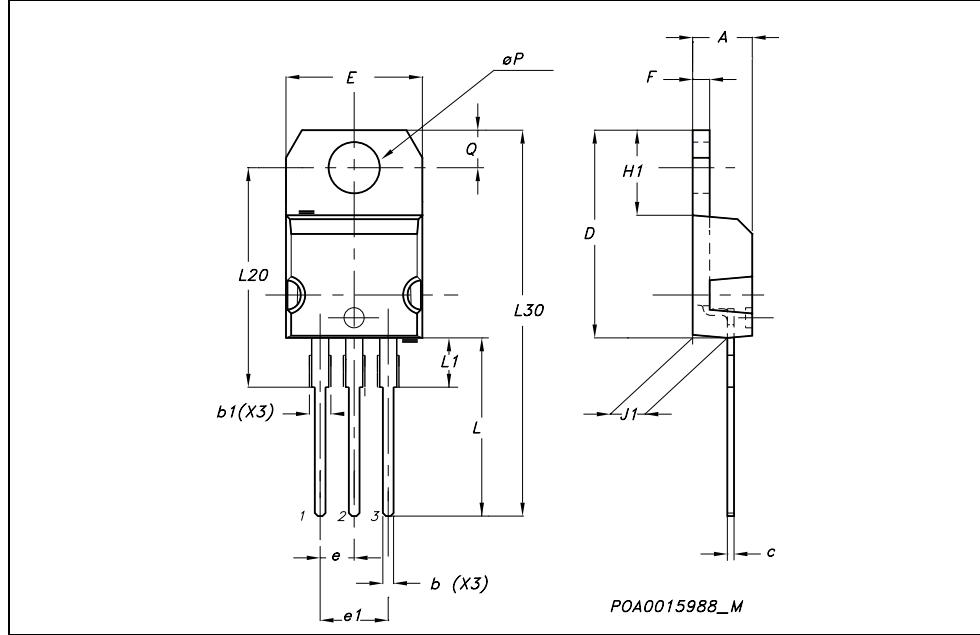


3 Package Mechanical Data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

TO-220 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	Typ.	MAX.	MIN.	Typ.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
ϕP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



4 Revision History

Date	Revision	Changes
27-Oct-2005	1	Initial Release

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